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Erratum: "High performance InGaZnO thin-film transistors with high-*k* amorphous $Ba_{0.5}Sr_{0.5}TiO_3$ gate insulator" [Appl. Phys. Lett. 93, 242111 (2008)]

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We mistakenly reported on thin-film transistors having a subthreshold slope of 0.06 ± 0.01 V/decade. The corrected value for the average and standard deviation of the subthreshold slope in these transistors should read 0.11 ± 0.02 V/decade.

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